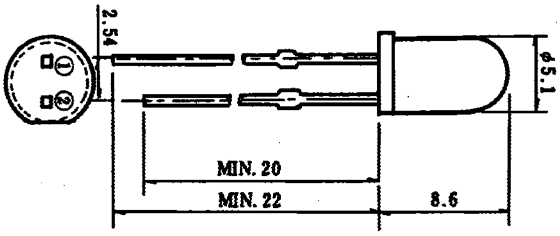
ML-217

INFRARED EMITTING DIODE

The ML-217 is a very high output infrared light emitting diode using GaAlAs chip. Its high output is equivalent to about 2 times than that of conventional products. In combining with MAL100 and CL138 (Photo darlington transistor). This device is most suitable for the application of remote control units, long distance photo electric switches and others.

Outline (typ)   Unit : mm



① Anode   ② Cathode

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A (Note)
Reverse Voltage (Continuous)	6V
Power Dissipation	175mW
Operating Temperature	-20 to +85°C
Lead Soldering Temperature (1/16" from case)	260°C

Note : Pulse Width = 10μs, Duty Ratio = 0.01

ELECTRO-OPTICAL CHARACTERISTICS ($T_A=25^\circ C$)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Radiant Power Output	Po	IF=50mA		15		mW
Spectrum Line Half Width	$\Delta\lambda$	IF=100mA		75		nm
Forward Voltage	VF	IF=100mA		1.7	2.0	V
Reverse Current	IR	VR=3V			10	μA
Peak Wavelength	λp	IF=100mA		880		nm

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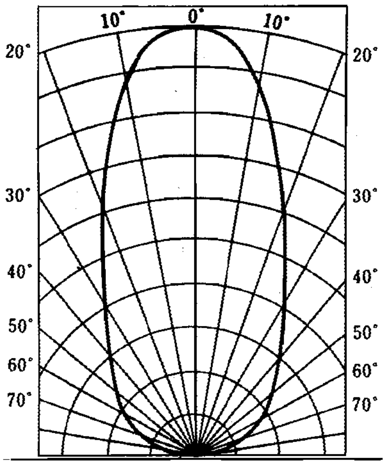
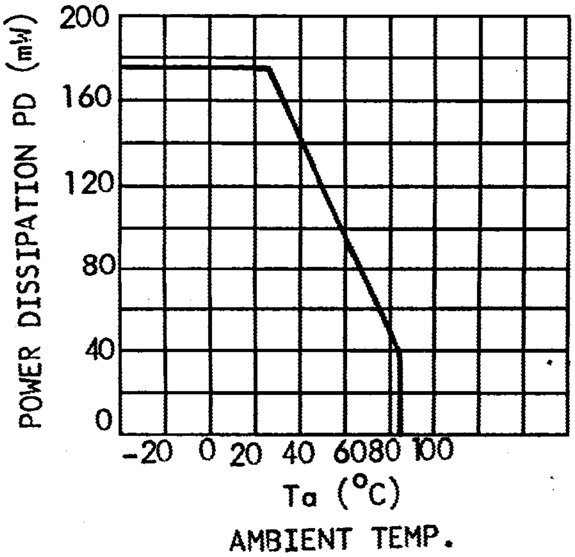
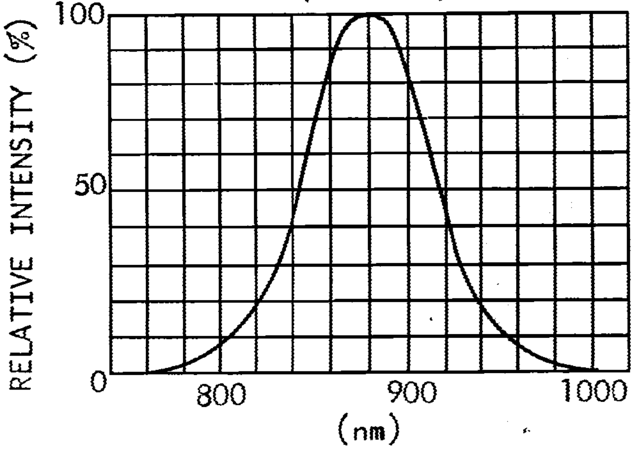
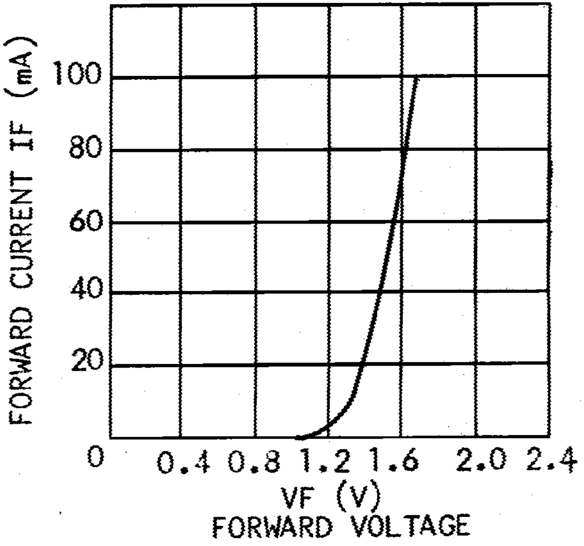
ML-217 TYPICAL CHARACTERISTICS


RADIATION PATTERN
(Ta=25°C)


POWER DISSIPATION


RELATIVE INTENSITY VS WAVELENGTH
(Ta=25°C)


FORWARD CURRENT VS FORWARD VOLTAGE
(Ta=25°C)

ML-217 TYPICAL CHARACTERISTICS

RADIANT POWER VS
FORWARD CURRENT
(Ta=25°C)